

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of claims

Claim 1. (currently amended) A method of fabricating a semiconductor wafer, comprising:

(a) disposing a volume of an aqueous slurry containing an abrasive material onto a semiconductor wafer and polishing the semiconductor wafer with a polishing pad; and

(b) disposing a volume of nonaqueous liquid including a nonaqueous solvent onto said semiconductor wafer to rinse the semiconductor wafer.

Claim 2 (canceled).

Claim 3. (currently amended) The method of claim 1, wherein:

said polishing pad is in contact with said semiconductor wafer when said volume of nonaqueous liquid solvent is disposed onto said semiconductor wafer.

Claim 4. (canceled)

Claim 5. (canceled)

Claim 6. (currently amended) The method of claim 23 5, wherein:

said weight % of said nonaqueous solvent in said aqueous slurry/nonaqueous solvent mixture is increased until said aqueous slurry/nonaqueous solvent mixture is substantially free of said aqueous slurry.

Claim 7. (original) The method of claim 1, wherein:

said nonaqueous solvent includes an ammine.

Claim 8. (original) The method of claim 1, wherein:

said nonaqueous solvent includes dimethylsulfoxide.

Claim 9. (original) The method of claim 1, wherein:

said nonaqueous solvent includes N,N-propanalamide.

Claim 10. (original) The method of claim 1, wherein:

said nonaqueous solvent includes analine.

Claim 11. (original) The method of claim 1, wherein:

said nonaqueous solvent includes N,N-dimethylaniline.

Claim 12. (currently amended) A method of fabricating a semiconductor wafer, comprising:

(a) subjecting a front side of said semiconductor wafer to chemical mechanical polishing using an aqueous slurry; and

(b) disposing a volume of nonaqueous liquid including a nonaqueous solvent onto said front side of said semiconductor wafer during said chemical mechanical polishing to rinse said semiconductor wafer.

Claim 13. (original) The method of claim 12, wherein:

said nonaqueous solvent includes an ammine.

Claim 14. (original) The method of claim 12, wherein:

said nonaqueous solvent includes dimethylsulfoxide.

Claim 15. (original) The method of claim 12, wherein:

said nonaqueous solvent includes N,N-propanalamide.

Claim 16. (original) The method of claim 12, wherein:

said nonaqueous solvent includes analine.

Claim 17. (original) The method of claim 12, wherein:

said nonaqueous solvent includes N,N-dimethylaniline.

Claims 18-20 (canceled).

Claim 21. (currently amended) A method of fabricating a semiconductor wafer, comprising:

(a) mixing an aqueous slurry containing an abrasive material and a nonaqueous solvent in a mixing unit so as to create a first volume of an aqueous slurry/nonaqueous solvent mixture with a first weight % of said nonaqueous solvent prior to being disposed onto said semiconductor wafer;

(b) disposing said first a volume of the aqueous slurry/nonaqueous solvent mixture containing an abrasive material onto said a semiconductor wafer; ~~and~~

(c) polishing the semiconductor wafer with a polishing pad using said first volume;

(d) mixing said aqueous slurry containing an abrasive material and said nonaqueous solvent so as to create a second volume of an aqueous slurry/nonaqueous solvent mixture having a greater weight % of said nonaqueous solvent than said first weight % prior to being disposed onto said semiconductor wafer;

(e) disposing said second volume of said aqueous slurry/nonaqueous solvent mixture containing an abrasive material onto said semiconductor wafer;
and

(f) polishing said semiconductor wafer using said second volume.

Claim 22. (new) The method of claim 21, further comprising:

reducing the pressure of said polishing pad on said semiconductor wafer after disposing said first volume of said aqueous slurry/nonaqueous solvent mixture onto said semiconductor wafer and before completing disposing said second volume of said aqueous slurry/nonaqueous solvent mixture onto said semiconductor wafer.

Claim 23. (new) The method of claim 21, wherein said disposing said second volume of aqueous slurry/nonaqueous solvent mixture further comprises:

disposing said second volume of aqueous slurry/nonaqueous solvent mixture during said polishing of said semiconductor wafer.

Claim 24. (new) The method of claim 23, wherein mixing said second volume of an aqueous slurry/nonaqueous solvent mixture is performed at least partially simultaneously with disposing said first volume onto said semiconductor wafer, and mixing said second volume comprises:

controlling a flow of said nonaqueous solvent into said mixing unit.

Claim 25. (new) The method of claim 3, further comprising:

reducing the pressure of said polishing pad on said semiconductor wafer prior to completing disposing a volume of nonaqueous liquid including a nonaqueous solvent onto said semiconductor wafer.

Claim 26. (new) The method of claim 12, further comprising:

reducing the pressure of a polishing pad on said front side of said semiconductor wafer prior to completing disposing a volume of nonaqueous liquid including a nonaqueous solvent onto said front side of said semiconductor wafer.